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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

E·XF

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I ² C, IrDA, LINbus, MMC/SD/SDIO, QSPI, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, LCD, POR, PWM, WDT
Number of I/O	50
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.8V
Data Converters	A/D 16x12b SAR; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	64-QFN (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg11b820f2048gm64-br

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3.10.2 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the microcontroller. The flash memory is readable and writable from both the Cortex-M and DMA. The flash memory is divided into two blocks; the main block and the information block. Program code is normally written to the main block, whereas the information block is available for special user data and flash lock bits. There is also a read-only page in the information block containing system and device calibration data. Read and write operations are supported in energy modes EM0 Active and EM1 Sleep.

3.10.3 Linked Direct Memory Access Controller (LDMA)

The Linked Direct Memory Access (LDMA) controller allows the system to perform memory operations independently of software. This reduces both energy consumption and software workload. The LDMA allows operations to be linked together and staged, enabling so-phisticated operations to be implemented.

3.10.4 Bootloader

All devices come pre-programmed with a UART bootloader. This bootloader resides in flash and can be erased if it is not needed. More information about the bootloader protocol and usage can be found in *AN0003: UART Bootloader*. Application notes can be found on the Silicon Labs website (www.silabs.com/32bit-appnotes) or within Simplicity Studio in the [**Documentation**] area.

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Max load current	I _{LOAD_MAX}	Low noise (LN) mode, Heavy Drive ² , T \leq 85 °C	_	-	200	mA
		Low noise (LN) mode, Heavy Drive ² , T > 85 °C	_	-	100	mA
		Low noise (LN) mode, Medium Drive ²	_	-	100	mA
		Low noise (LN) mode, Light Drive ²	_	-	50	mA
		Low power (LP) mode, LPCMPBIASEMxx ³ = 0	_	-	75	μA
		Low power (LP) mode, LPCMPBIASEMxx ³ = 3	_	-	10	mA
DCDC nominal output ca- pacitor ⁵	C _{DCDC}	25% tolerance	1	4.7	4.7	μF
DCDC nominal output induc- tor	L _{DCDC}	20% tolerance	4.7	4.7	4.7	μH
Resistance in Bypass mode	R _{BYP}		-	1.2	2.5	Ω

Note:

1. Due to internal dropout, the DC-DC output will never be able to reach its input voltage, V_{VREGVDD}.

- 2. Drive levels are defined by configuration of the PFETCNT and NFETCNT registers. Light Drive: PFETCNT=NFETCNT=3; Medium Drive: PFETCNT=NFETCNT=7; Heavy Drive: PFETCNT=15.
- 3. LPCMPBIASEMxx refers to either LPCMPBIASEM234H in the EMU_DCDCMISCCTRL register or LPCMPBIASEM01 in the EMU_DCDCLOEM01CFG register, depending on the energy mode.

4. LP mode controller is a hysteretic controller that maintains the output voltage within the specified limits.

5. Output voltage under/over-shoot and regulation are specified with C_{DCDC} 4.7 μF. Different settings for DCDCLNCOMPCTRL must be used if C_{DCDC} is lower than 4.7 μF. See Application Note AN0948 for details.

4.1.7 Current Consumption

4.1.7.1 Current Consumption 3.3 V without DC-DC Converter

Unless otherwise indicated, typical conditions are: VREGVDD = AVDD = DVDD = 3.3 V. T = 25 °C. DCDC is off. Minimum and maximum values in this table represent the worst conditions across supply voltage and process variation at T = 25 °C.

Table 4.7. Current Consumption 3.3 V without DC-DC Converter

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Current consumption in EM0 mode with all peripherals dis-	I _{ACTIVE}	72 MHz HFRCO, CPU running Prime from flash	_	120	_	µA/MHz
abled		72 MHz HFRCO, CPU running while loop from flash	_	120	TBD	µA/MHz
		72 MHz HFRCO, CPU running CoreMark loop from flash	_	140		µA/MHz
		50 MHz crystal, CPU running while loop from flash	_	123	_	µA/MHz
		48 MHz HFRCO, CPU running while loop from flash	_	122	TBD	µA/MHz
		32 MHz HFRCO, CPU running while loop from flash	_	124	_	µA/MHz
		26 MHz HFRCO, CPU running while loop from flash	_	126	TBD	µA/MHz
		16 MHz HFRCO, CPU running while loop from flash	_	131	_	µA/MHz
		1 MHz HFRCO, CPU running while loop from flash	_	319	TBD	µA/MHz
Current consumption in EM0 mode with all peripherals dis-	IACTIVE_VS	19 MHz HFRCO, CPU running while loop from flash	_	107	_	µA/MHz
abled and voltage scaling enabled		1 MHz HFRCO, CPU running while loop from flash	_	262	_	µA/MHz
Current consumption in EM1	I _{EM1}	72 MHz HFRCO	—	57	TBD	µA/MHz
mode with all peripherals disabled		50 MHz crystal	_	60	_	µA/MHz
		48 MHz HFRCO	_	59	TBD	µA/MHz
		32 MHz HFRCO	_	61		µA/MHz
		26 MHz HFRCO		63	TBD	µA/MHz
		16 MHz HFRCO		68	_	µA/MHz
		1 MHz HFRCO	_	255	TBD	µA/MHz
Current consumption in EM1	I _{EM1_VS}	19 MHz HFRCO	_	55	_	µA/MHz
mode with all peripherals dis- abled and voltage scaling enabled		1 MHz HFRCO	_	210	_	µA/MHz

Parameter	Symbol	Test Condition	Min	Тур	Мах	Unit
ADC clock frequency	f _{ADCCLK}		—	—	16	MHz
Throughput rate	f ADCRATE		_	_	1	Msps
Conversion time ¹	t _{ADCCONV}	6 bit	—	7	_	cycles
		8 bit	_	9	_	cycles
		12 bit	—	13		cycles
Startup time of reference generator and ADC core	t _{ADCSTART}	WARMUPMODE ⁴ = NORMAL	—	_	5	μs
		WARMUPMODE ⁴ = KEEPIN- STANDBY	_	_	2	μs
		WARMUPMODE ⁴ = KEEPINSLO- WACC	_	_	1	μs
SNDR at 1Msps and f _{IN} = 10kHz	SNDR _{ADC}	Internal reference ⁷ , differential measurement	TBD	67	_	dB
		External reference ⁶ , differential measurement	_	68	_	dB
Spurious-free dynamic range (SFDR)	SFDR _{ADC}	1 MSamples/s, 10 kHz full-scale sine wave	_	75	_	dB
Differential non-linearity (DNL)	DNL _{ADC}	12 bit resolution, No missing co- des	TBD		TBD	LSB
Integral non-linearity (INL), End point method	INL _{ADC}	12 bit resolution	TBD		TBD	LSB
Offset error	VADCOFFSETERR		TBD	0	TBD	LSB
Gain error in ADC	VADCGAIN	Using internal reference	_	-0.2	TBD	%
		Using external reference	_	-1	—	%
Temperature sensor slope	V _{TS_SLOPE}		_	-1.84	_	mV/°C

Note:

1. Derived from ADCCLK.

2. PSRR is referenced to AVDD when ANASW=0 and to DVDD when ANASW=1 in EMU_PWRCTRL.

3. In ADCn_BIASPROG register.

4. In ADCn CNTL register.

5. The absolute voltage allowed at any ADC input is dictated by the power rail supplied to on-chip circuitry, and may be lower than the effective full scale voltage. All ADC inputs are limited to the ADC supply (AVDD or DVDD depending on EMU PWRCTRL ANASW). Any ADC input routed through the APORT will further be limited by the IOVDD supply to the pin.

6. External reference is 1.25 V applied externally to ADCnEXTREFP, with the selection CONF in the SINGLECTRL_REF or SCANCTRL_REF register field and VREFP in the SINGLECTRLX_VREFSEL or SCANCTRLX_VREFSEL field. The differential input range with this configuration is ± 1.25 V.

7. Internal reference option used corresponds to selection 2V5 in the SINGLECTRL_REF or SCANCTRL_REF register field. The differential input range with this configuration is ± 1.25 V. Typical value is characterized using full-scale sine wave input. Minimum value is production-tested using sine wave input at 1.5 dB lower than full scale.

4.1.23.2 I2C Fast-mode (Fm)¹

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
SCL clock frequency ²	f _{SCL}		0	_	400	kHz
SCL clock low time	t _{LOW}		1.3	_	_	μs
SCL clock high time	t _{HIGH}		0.6	_	_	μs
SDA set-up time	t _{SU_DAT}		100	_	_	ns
SDA hold time ³	t _{HD_DAT}		100	_	900	ns
Repeated START condition set-up time	t _{SU_STA}		0.6	_	_	μs
(Repeated) START condition hold time	t _{HD_STA}		0.6	_	_	μs
STOP condition set-up time	t _{SU_STO}		0.6	_		μs
Bus free time between a STOP and START condition	t _{BUF}		1.3	—	_	μs

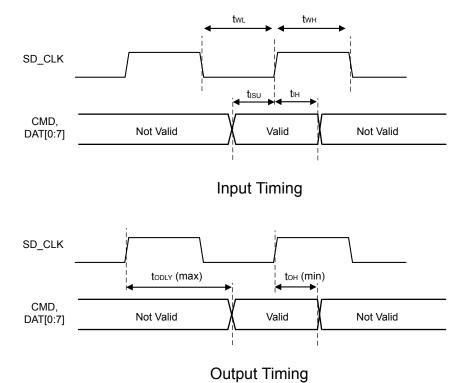
Table 4.32. I2C Fast-mode (Fm)¹

Note:

1. For CLHR set to 1 in the I2Cn_CTRL register.

2. For the minimum HFPERCLK frequency required in Fast-mode, refer to the I2C chapter in the reference manual.

3. The maximum SDA hold time (t_{HD,DAT}) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).



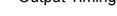


Figure 4.14. SDIO HS Mode Timing

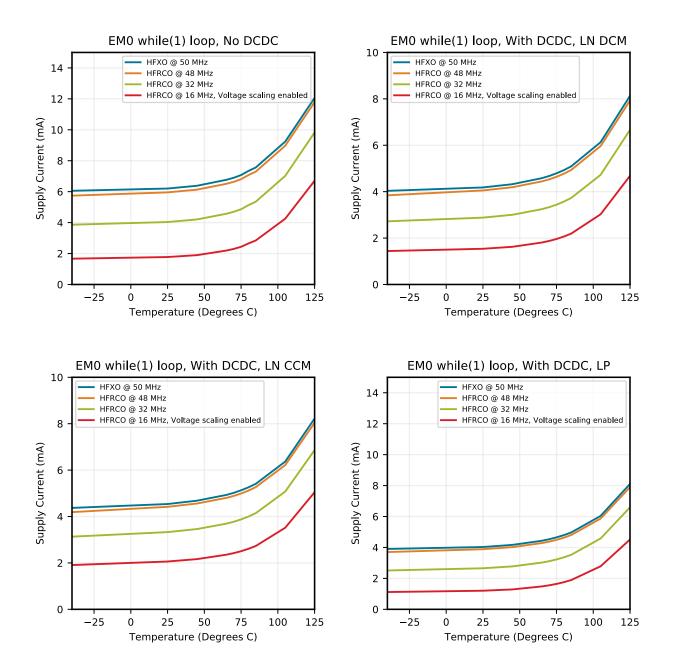


Figure 4.24. EM0 Active Mode Typical Supply Current vs. Temperature

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PB2	M2	GPIO	PB3	M3	GPIO
PC6	M14	GPIO	VREGVSS	M15 N16	Voltage regulator VSS
VREGSW	M16	DCDC regulator switching node	PB4	N1	GPIO
PB5	N2	GPIO	PB6	N3	GPIO
PD5	N14	GPIO	PD4	N15	GPIO
PC0	P1	GPIO (5V)	PC1	P2	GPIO (5V)
PC2	P3	GPIO (5V)	PA8	P4	GPIO
PA11	P5	GPIO	PA13	P6	GPIO (5V)
PB9	P7	GPIO (5V)	PB12	P8	GPIO
PH2	P9	GPIO (5V)	PH5	P10	GPIO
PH8	P11	GPIO (5V)	PH11	P12	GPIO (5V)
PH13	P13	GPIO (5V)	PD0	P14	GPIO (5V)
PD3	P15	GPIO	PD8	P16	GPIO
PB7	R1	GPIO	PC3	R2	GPIO (5V)
PC5	R3	GPIO	PA9	R4	GPIO
BODEN	R5	Brown-Out Detector Enable. This pin may be left disconnected or tied to AVDD.	RESETn	R6	Reset input, active low. To apply an ex- ternal reset source to this pin, it is re- quired to only drive this pin low during reset, and let the internal pull-up ensure that reset is released.
PB10	R7	GPIO (5V)	PH0	R8	GPIO (5V)
PH3	R9	GPIO (5V)	PH6	R10	GPIO
PH9	R11	GPIO (5V)	PH12	R12	GPIO (5V)
PH14	R13	GPIO (5V)	PH15	R14	GPIO (5V)
PD2	R15	GPIO (5V)	PD7	R16	GPIO
PB8	T1	GPIO	PC4	T2	GPIO
PA7	Т3	GPIO	PA10	T4	GPIO
PA12	T5	GPIO (5V)	PA14	Т6	GPIO
PB11	T7	GPIO	PH1	Т8	GPIO (5V)
PH4	Т9	GPIO	PH7	T10	GPIO (5V)
PH10	T11	GPIO (5V)	PB13	T12	GPIO
PB14	T13	GPIO	AVDD	T14	Analog power supply.
PD1	T15	GPIO	PD6	T16	GPIO

Note:

1. GPIO with 5V tolerance are indicated by (5V).

2. The pins PD13, PD14, and PD15 will not be 5V tolerant on all future devices. In order to preserve upgrade options with full hardware compatibility, do not use these pins with 5V domains.

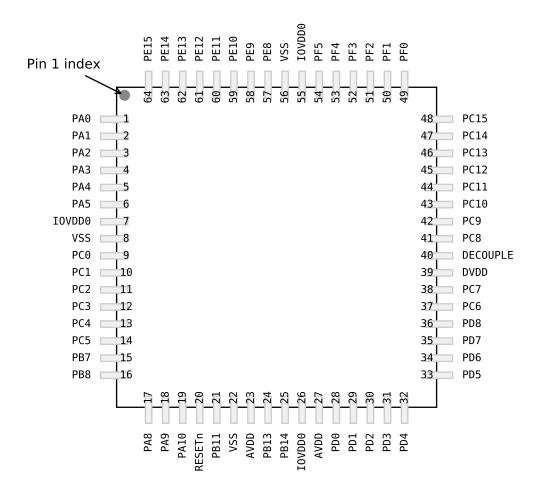


Figure 5.15. EFM32GG11B1xx in QFP64 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see 5.20 GPIO Functionality Table or 5.21 Alternate Functionality Overview.

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PA0	1	GPIO	PA1	2	GPIO
PA2	3	GPIO	PA3	4	GPIO
PA4	5	GPIO	PA5	6	GPIO
IOVDD0	7 26 55	Digital IO power supply 0.	VSS	8 22 56	Ground
PC0	9	GPIO (5V)	PC1	10	GPIO (5V)
PC2	11	GPIO (5V)	PC3	12	GPIO (5V)

GPIO Name	Pin Alternate Functionality / Description					
	Analog	EBI	Timers	Communication	Other	
PB13	BUSAY BUSBX HFXTAL_P		TIM6_CC0 #5 WTIM1_CC0 #0 PCNT2_S0IN #2	US0_CLK #4 US1_CTS #5 US5_CS #0 LEU0_TX #1	CMU_CLKI0 #3 PRS_CH7 #0	
PB14	BUSBY BUSAX HFXTAL_N		TIM6_CC1 #5 WTIM1_CC1 #0 PCNT2_S1IN #2	US0_CS #4 US1_RTS #5 US5_CTS #0 LEU0_RX #1	PRS_CH6 #1	
PD1	VDAC0_OUT1ALT / OPA1_OUTALT #4 BUSADC0Y BU- SADC0X OPA3_OUT	EBI_A05 #1 EBI_A14 #3	TIM4_CDTI1 TIM0_CC0 #2 TIM6_CC0 #6 WTIM1_CC3 #0 PCNT2_S1IN #0	CAN0_TX #2 US1_RX #1	DBG_SWO #2	
PD6	BUSADC0Y BU- SADC0X ADC0_EXTP VDAC0_EXT ADC1_EXTP OPA1_P	EBI_A10 #1 EBI_A19 #3	TIM1_CC0 #4 TIM6_CC2 #7 WTIM0_CDTI2 #4 WTIM1_CC0 #2 LE- TIM0_OUT0 #0 PCNT0_S0IN #3	US0_RTS #5 US1_RX #2 US2_CTS #5 US3_CTS #2 U0_RTS #5 I2C0_SDA #1	CMU_CLK2 #2 LES_ALTEX0 PRS_CH5 #2 ACMP0_O #2 ETM_TD0 #0	

Alternate	LOCATION		
Functionality	0 - 3	4 - 7	Description
EBI_AD08	0: PA15 1: PC1 2: PG8		External Bus Interface (EBI) address and data input / output pin 08.
EBI_AD09	0: PA0 1: PC2 2: PG9		External Bus Interface (EBI) address and data input / output pin 09.
EBI_AD10	0: PA1 1: PC3 2: PG10		External Bus Interface (EBI) address and data input / output pin 10.
EBI_AD11	0: PA2 1: PC4 2: PG11		External Bus Interface (EBI) address and data input / output pin 11.
EBI_AD12	0: PA3 1: PC5 2: PG12		External Bus Interface (EBI) address and data input / output pin 12.
EBI_AD13	0: PA4 1: PA7 2: PG13		External Bus Interface (EBI) address and data input / output pin 13.
EBI_AD14	0: PA5 1: PA8 2: PG14		External Bus Interface (EBI) address and data input / output pin 14.
EBI_AD15	0: PA6 1: PA9 2: PG15		External Bus Interface (EBI) address and data input / output pin 15.
EBI_ALE	0: PF3 1: PB9 2: PC4 3: PB5	4: PC11 5: PC11	External Bus Interface (EBI) Address Latch Enable output.
EBI_ARDY	0: PF2 1: PD13 2: PB15 3: PB4	4: PC13 5: PF10	External Bus Interface (EBI) Hardware Ready Control input.
EBI_BL0	0: PF6 1: PF8 2: PB10 3: PC1	4: PF6 5: PF6	External Bus Interface (EBI) Byte Lane/Enable pin 0.
EBI_BL1	0: PF7 1: PF9 2: PB11 3: PC3	4: PF7 5: PF7	External Bus Interface (EBI) Byte Lane/Enable pin 1.
EBI_CS0	0: PD9 1: PA10 2: PC0 3: PB0	4: PE8	External Bus Interface (EBI) Chip Select output 0.

Alternate	LOCATION		
Functionality	0 - 3	4 - 7	Description
EBI_CS1	0: PD10 1: PA11 2: PC1 3: PB1	4: PE9	External Bus Interface (EBI) Chip Select output 1.
EBI_CS2	0: PD11 1: PA12 2: PC2 3: PB2	4: PE10	External Bus Interface (EBI) Chip Select output 2.
EBI_CS3	0: PD12 1: PB15 2: PC3 3: PB3	4: PE11	External Bus Interface (EBI) Chip Select output 3.
EBI_CSTFT	0: PA7 1: PF6 2: PB12 3: PA0		External Bus Interface (EBI) Chip Select output TFT.
EBI_DCLK	0: PA8 1: PF7 2: PH0 3: PA1		External Bus Interface (EBI) TFT Dot Clock pin.
EBI_DTEN	0: PA9 1: PD9 2: PH1 3: PA2		External Bus Interface (EBI) TFT Data Enable pin.
EBI_HSNC	0: PA11 1: PD11 2: PH3 3: PA4		External Bus Interface (EBI) TFT Horizontal Synchronization pin.
EBI_NANDREn	0: PC3 1: PD15 2: PB9 3: PC4	4: PC15 5: PF12	External Bus Interface (EBI) NAND Read Enable output.
EBI_NANDWEn	0: PC5 1: PD14 2: PA13 3: PC2	4: PC14 5: PF11	External Bus Interface (EBI) NAND Write Enable output.
EBI_REn	0: PF5 1: PA14 2: PA12 3: PC0	4: PF9 5: PF5	External Bus Interface (EBI) Read Enable output.
EBI_VSNC	0: PA10 1: PD10 2: PH2 3: PA3		External Bus Interface (EBI) TFT Vertical Synchronization pin.
EBI_WEn	0: PF4 1: PA13 2: PC5 3: PB6	4: PF8 5: PF4	External Bus Interface (EBI) Write Enable output.
ETH_MDC	0: PB4 1: PD14 2: PC1 3: PA6		Ethernet Management Data Clock.

Alternate	LOCA	TION	
Functionality	0 - 3	4 - 7	Description
ETH_MDIO	0: PB3 1: PD13 2: PC0 3: PA15		Ethernet Management Data I/O.
ETH_MIICOL	0: PB2 1: PG15 2: PB4		Ethernet MII Collision Detect.
ETH_MIICRS	0: PB1 1: PG14 2: PB3		Ethernet MII Carrier Sense.
ETH_MIIRXCLK	0: PA15 1: PG7 2: PD12		Ethernet MII Receive Clock.
ETH_MIIRXD0	0: PE12 1: PG11 2: PF9		Ethernet MII Receive Data Bit 0.
ETH_MIIRXD1	0: PE13 1: PG10 2: PD9		Ethernet MII Receive Data Bit 1.
ETH_MIIRXD2	0: PE14 1: PG9 2: PD10		Ethernet MII Receive Data Bit 2.
ETH_MIIRXD3	0: PE15 1: PG8 2: PD11		Ethernet MII Receive Data Bit 3.
ETH_MIIRXDV	0: PE11 1: PG12 2: PF8		Ethernet MII Receive Data Valid.
ETH_MIIRXER	0: PE10 1: PG13 2: PF7		Ethernet MII Receive Error.
ETH_MIITXCLK	0: PA0 1: PG0		Ethernet MII Transmit Clock.
ETH_MIITXD0	0: PA4 1: PG4		Ethernet MII Transmit Data Bit 0.
ETH_MIITXD1	0: PA3 1: PG3		Ethernet MII Transmit Data Bit 1.

Alternate	LOCATION			
Functionality	0 - 3	4 - 7	Description	
ETH_MIITXD2	0: PA2 1: PG2		Ethernet MII Transmit Data Bit 2.	
ETH_MIITXD3	0: PA1 1: PG1		Ethernet MII Transmit Data Bit 3.	
ETH_MIITXEN	0: PA5 1: PG5		Ethernet MII Transmit Enable.	
ETH_MIITXER	0: PA6 1: PG6		Ethernet MII Transmit Error.	
ETH_RMIICRSDV	0: PA4 1: PD11		Ethernet RMII Carrier Sense / Data Valid.	
ETH_RMIIREFCLK	0: PA3 1: PD10		Ethernet RMII Reference Clock.	
ETH_RMIIRXD0	0: PA2 1: PD9		Ethernet RMII Receive Data Bit 0.	
ETH_RMIIRXD1	0: PA1 1: PF9		Ethernet RMII Receive Data Bit 1.	
ETH_RMIIRXER	0: PA5 1: PD12		Ethernet RMII Receive Error.	
ETH_RMIITXD0	0: PE15 1: PF7		Ethernet RMII Transmit Data Bit 0.	
ETH_RMIITXD1	0: PE14 1: PF6		Ethernet RMII Transmit Data Bit 1.	
ETH_RMIITXEN	0: PA0 1: PF8		Ethernet RMII Transmit Enable.	
ETH_TSUEXTCLK	0: PB5 1: PD15 2: PC2 3: PF8		Ethernet IEEE1588 External Reference Clock.	

Alternate Functionality	Location	Priority		
QSPI0_DQS	0: PF9	High Speed		
QSPI0_SCLK	0: PF6	High Speed		
SDIO_CLK	0: PE13	High Speed		
SDIO_CMD	0: PE12	High Speed		
SDIO_DAT0	0: PE11	High Speed		
SDIO_DAT1	0: PE10	High Speed		
SDIO_DAT2	0: PE9	High Speed		
SDIO_DAT3	0: PE8	High Speed		
SDIO_DAT4	0: PD12	High Speed		
SDIO_DAT5	0: PD11	High Speed		
SDIO_DAT6	0: PD10	High Speed		
SDIO_DAT7	0: PD9	High Speed		
TIM0_CC0	3: PB6	Non-interference		
TIM0_CC1	3: PC0	Non-interference		
TIM0_CC2	3: PC1	Non-interference		
TIM0_CDTI0	1: PC13	Non-interference		
TIM0_CDTI1	1: PC14	Non-interference		
TIM0_CDTI2	1: PC15	Non-interference		
TIM2_CC0	0: PA8	Non-interference		
TIM2_CC1	0: PA9	Non-interference		
TIM2_CC2	0: PA10	Non-interference		
TIM2_CDTI0	0: PB0	Non-interference		
TIM2_CDTI1	0: PB1	Non-interference		
TIM2_CDTI2	0: PB2	Non-interference		
TIM4_CC0	0: PF3	Non-interference		
TIM4_CC1	0: PF4	Non-interference		
TIM4_CC2	0: PF12	Non-interference		
TIM4_CDTI0	0: PD0	Non-interference		
TIM4_CDTI1	0: PD1	Non-interference		
TIM4_CDTI2	0: PD3	Non-interference		
TIM6_CC0	0: PG0	Non-interference		
TIM6_CC1	0: PG1	Non-interference		
TIM6_CC2	0: PG2	Non-interference		
TIM6_CDTI0	0: PG3	Non-interference		
TIM6_CDTI1	0: PG4	Non-interference		
TIM6_CDTI2	0: PG5	Non-interference		

6. BGA192 Package Specifications

6.1 BGA192 Package Dimensions

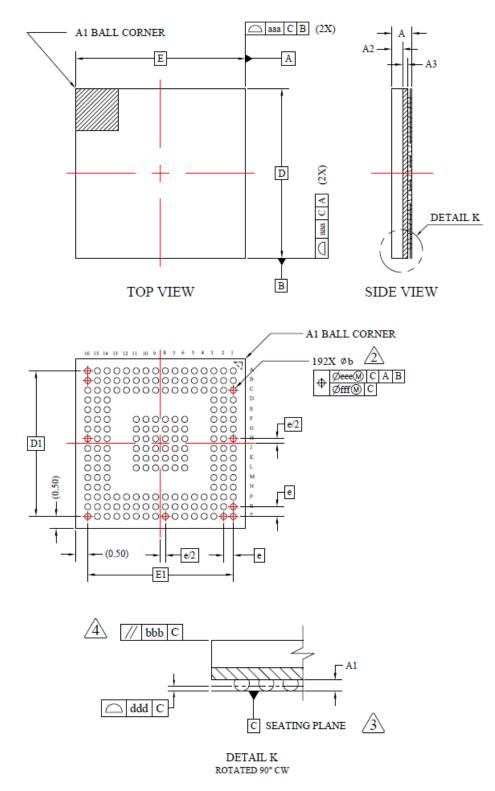


Figure 6.1. BGA192 Package Drawing

Table 8.2. BGA120 PCB Land Pattern Dimensions

Min	Nom	Мах	
0.20			
6.00			
6.00			
0.5			
	0.5		
	Min	0.20 6.00 6.00 0.5	

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.

2. Dimensioning and Tolerancing is per the ANSI Y14.5M-1994 specification.

3. This Land Pattern Design is based on the IPC-7351 guidelines.

4. All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 μm minimum, all the way around the pad.

5. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.

6. The stencil thickness should be 0.125 mm (5 mils).

7. The ratio of stencil aperture to land pad size should be 1:1.

8. A No-Clean, Type-3 solder paste is recommended.

9. The recommended card reflow profile is per the JEDEC/IPC J-STD-020C specification for Small Body Components.

9.2 BGA112 PCB Land Pattern

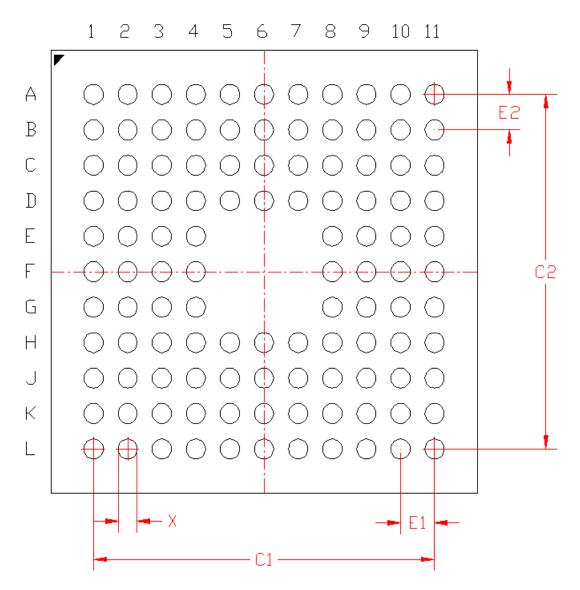


Figure 9.2. BGA112 PCB Land Pattern Drawing



Figure 9.3. BGA112 Package Marking

The package marking consists of:

- PPPPPPPPP The part number designation.
- TTTTTT A trace or manufacturing code. The first letter is the device revision.
- YY The last 2 digits of the assembly year.
- WW The 2-digit workweek when the device was assembled.

Table 10.2. TQFP100 PCB Land Pattern Dimensions

Min	Nom	Мах		
15.4				
15.4				
0.50 BSC				
0.30				
1.50				
	Min	15.4 15.4 0.50 BSC 0.30		

Note:

- 1. All dimensions shown are in millimeters (mm) unless otherwise noted.
- 2. This Land Pattern Design is based on the IPC-7351 guidelines.
- 3. All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 µm minimum, all the way around the pad.
- 4. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release. 5. The stencil thickness should be 0.125 mm (5 mils).
- 6. The ratio of stencil aperture to land pad size should be 1:1 for all perimeter pads.
- 7. A No-Clean, Type-3 solder paste is recommended.
- 8. The recommended card reflow profile is per the JEDEC/IPC J-STD-020C specification for Small Body Components.

10.3 TQFP100 Package Marking



Figure 10.3. TQFP100 Package Marking

The package marking consists of:

- PPPPPPPP The part number designation.
- TTTTTT A trace or manufacturing code. The first letter is the device revision.
- YY The last 2 digits of the assembly year.
- · WW The 2-digit workweek when the device was assembled.